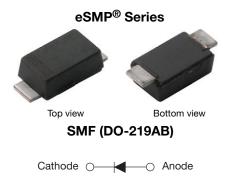
RoHS

COMPLIANT HALOGEN

FREE

Vishay Semiconductors

Hyperfast Rectifier, 1 A FRED Pt®



click logo to get started

www.vishay.com

DESIGN SUPPORT TOOLS



PRIMARY CHARACTERISTICS					
I _{F(AV)}	1 A				
V _R	200 V				
V _F at I _F (typ. 125 °C)	0.74 V				
t _{rr}	25 ns				
T _J max.	175 °C				
Package	SMF (DO-219AB)				
Circuit configuration	Single				

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Wave and reflow solderable
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V _{RRM}		200	V			
Average rectified forward current	I _{F(AV)}	$T_{\rm C} = 160 \ ^{\circ}{\rm C} \ ^{(1)}$	1	^			
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	35	A			
Operating junction and storage temperature range	T _J , T _{Stg}		-65 to +175	°C			

Note

(1) Device on PCB with 8 mm x 16 mm soldering lands

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R I _R = 100 μA		200	-	-		
Forward voltage	V _F	I _F = 1 A	-	0.87	0.93	V	
		I _F = 1 A, T _J = 125 °C	-	0.74	0.8		
Reverse leakage current I _R		$V_{R} = V_{R}$ rated	-	-	2		
		$T_J = 125 \ ^{\circ}C, V_R = V_R \text{ rated}$	-	1	8	μA	
Junction capacitance	C _T	V _R = 200 V	-	5	-	pF	

Revision: 10-Aug-2018

1

Document Number: 95785

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}$	õs, V _R = 30 V	-	24	-		
Reverse recovery time	+	$I_{F} = 0.5 \text{ A}, I_{R} = 1 \text{ A}, I_{rr}$	-	-	25			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	16	-	ns	
		T _J = 125 °C		-	23	-		
Deck receiver a surrent		T _J = 25 °C	$I_F = 1 A$	-	1.6	-	^	
Peak recovery current	I _{RRM}	T _J = 125 °C	dl _F /dt = 200 A/µs V _R = 160 V	-	2.5	-	A	
D	0	T _J = 25 °C]	-	13	-		
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	30	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	+175	°C	
Thermal resistance, junction to case	R _{thJC}	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	17	°C/W	
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	140	°C/W	
Approximate weight				0.015		g	
Approximate weight				0.0005		oz.	
Marking device		Case style SMF (DO-219AB)		М	DH		

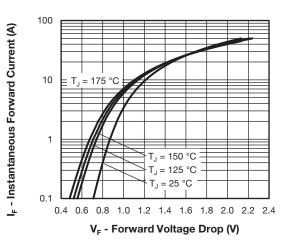


Fig. 1 - Typical Forward Voltage Drop Characteristics

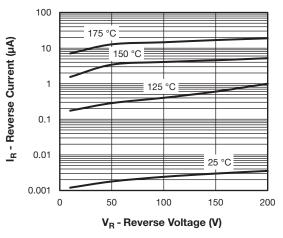


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



Vishay Semiconductors



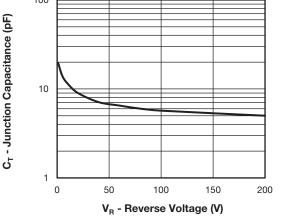


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

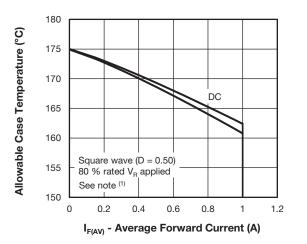


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

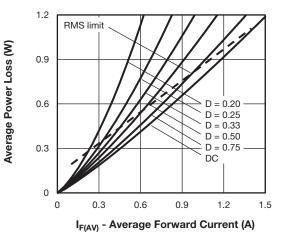


Fig. 5 - Forward Power Loss Characteristics

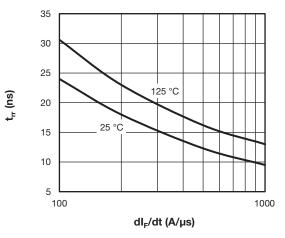


Fig. 6 - Typical Reverse Recovery Time vs. dl_F/dt

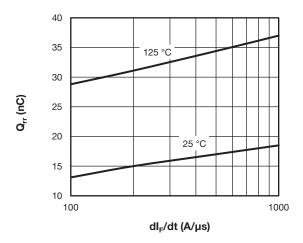


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ 5); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

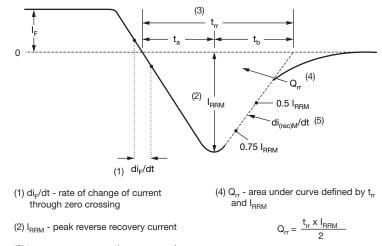
3

Document Number: 95785

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

VS-1EFH02-M3

Vishay Semiconductors



(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(5) di_{(rec)M}/dt - peak rate of change of current during $t_{\rm b}$ portion of $t_{\rm rr}$

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

www.vishay.com

Device code	VS-	1	Е	F	н	02	-МЗ
		(2)	(3)	(4)	(5)	(6)	(7)
	1	- Visl	nay Sen	nicondu	ctors pr	oduct	U
	2		-	ng (1 =			
	3 -			figuratio	n:		
	_	E =	single c	liode			
	4	- F=	SMF pa	ackage			
	5 -	- Pro	cess typ	be,			
		H =	hyperfa	ast recov	very		
	6	- Vol	tage coo	de (02 =	200 V)		
	7	M3	B = halog	gen-free	e, RoHS	-compli	iant, and

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTIO						
VS-1EFH02-M3/I	10 000	10 000	13"diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95572				
Part marking information	www.vishay.com/doc?95618				
Packaging information	www.vishay.com/doc?95577				
SPICE model	www.vishay.com/doc?96012				

 Revision: 10-Aug-2018
 4
 Document Number: 95785

 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
 DiodesEurope@vishay.com

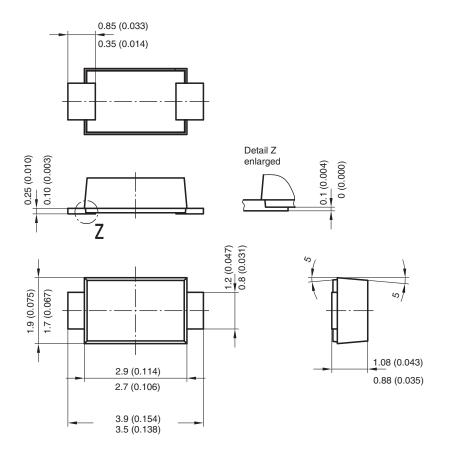
 THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



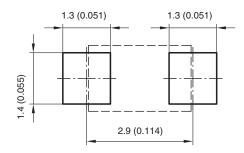
Vishay Semiconductors

SMF (DO-219AB)

DIMENSIONS in millimeters (inches)



Foot print recommendation:



Created - Date: 15. February 2005 Rev. 3 - Date: 13. March 2007 Document no.:S8-V-3915.01-001 (4) 17247



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Vishay: VS-1EFH02-M3/I